## AMT1223(L1) 0.1 – 10GHz Low Noise Amplifier Chip

#### **Key Features:**

• Frequency range: 0.1 – 10GHz

• Typical gain: 23dB

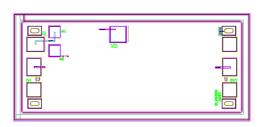
Input standing wave : 1.4Output standing wave : 1.4

• Noise figure: 2dB

P-1: 12dBm @ +5V/55mA

• Chip dimensions: 1.5mm x 0.65mm x 0.1mm

• Applications: wireless communication, transceiver module, radio telecommunication etc.



### **Description:**

AMT1223(L1) chip is a Gallium Arsenide (GaAs) high performance Low Noise Amplifier, it covers 0.1 – 10GHz frequency range. It uses +5V single voltage operation, noise figure is 2dB, and 23dB typical gain. This chip is designed with ground through metal vias on the back technology.

#### **Absolute Maximum Ratings (Ta = 25°C)**

Symbol	Parameter	Value	Remark		
Vd	Drain Voltage	+6V			
Pin	Input Signal Power	17dBm			
Tch	Operating Temperature	150°C			
Tm	Sintering Temperature	310°C	30s, N <sub>2</sub> protection		
Tstg	Storage Temperature	-65 ~ +150°C			

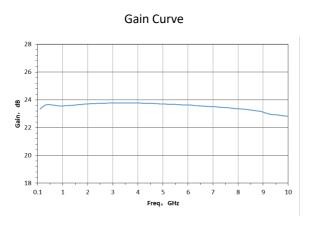
<sup>[1]</sup> Operation outside any of the Absolute Maximum Ratings may cause permanent device damage.

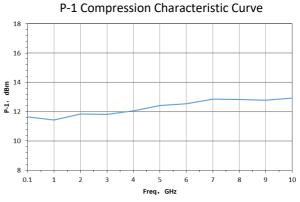
## **Electrical Characteristics (Ta = 25°C)**

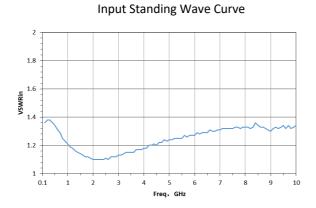
Symbol	Parameter	<b>Test Conditions</b>	Value		Unit	
			Min	Typical	Max	
G	Gain		-	23	-	dB
NF	Noise Figure		-	2	-	dB
Id	Static Current	Vd = +5V	-	55	-	mA
VSWR_in	Input Standing Wave	F: 0.1 ~ 10GHz	-	1.4	-	-
VSWR_out	Output Standing Wave		-	1.4	-	-
P-1	Output Power at 1dB point		-	12	-	dBm

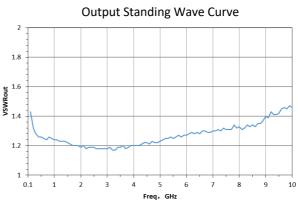
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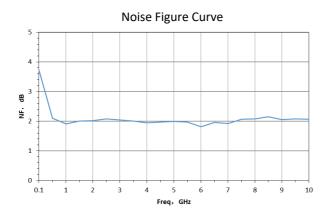
## **Typical Performance**





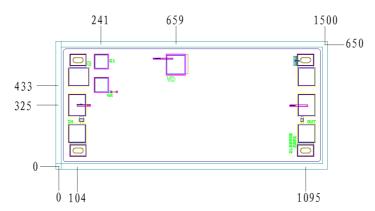




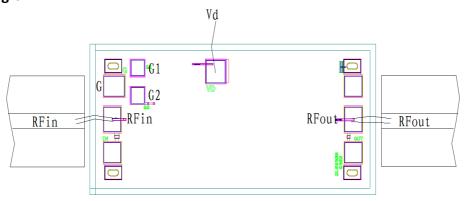


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# Chip Dimensions (Unit: $\mu$ m)



## **Chip Layout Diagram**



#### **Pad Definition**

Symbol	Function Description	Demensions	<b>Equivalent Circuit</b>
RFin	RF signal input port, connecting to external 50 $\!\Omega$ system, need to add DC blocking capacitor.	100μm*100μm	RF-in
RFout	RF signal output port, connecting to external $50\Omega$ system, need to add DC blocking capacitor.	100μm*100μm	RF-out
Vd	Amplifier bias, need to connect 100pF external capacitor	100μm*100μm	VD CHIP

Please see Appendix A for details.